InGrid, an integrated Micromegas made in Silicon wafer post-processing technology

M. Chefdeville^a , P. Colas^b, Y. Giomataris^b, H. van der Graaf^a, E.H.M.Heijne^c, S.van der Putten^a, C. Salm^d, J. Schmitz^d, S. Smits^d, J. Timmermans^a, J.L. Visschers^a a) NI KHEF Amsterdam, b) DAPNI A Saclay, c) CERN, d) Twente University/MESA+



- Motivation
- Process
- •First results
- •Future

Reminder : Micromegas + pixels

MICROMEsh GASeous detector :

Amplification region : 50-100 micron gap Amplification field >> drift field => efficient collection

Gap small => fast signals

Optimally, anode pad size can be = hole pitch ->VLSI (CMOS) electronics (Medipix2) 65000 pixels on 2cm²



S2

NIKHEF-Saclay CERN Twente Collaboration since early 2004





He/I sobutane 80/20 Modified MediPix (80% of the pixel is conductive, instead of 20%)

Cluster by cluster **MIP** detection

Very

but...



Snowmass, August, 2005

P. Colas - InGrid

But...

- •Moiré effect: pitch Micromegas holes: 60 µm pitch MediPix pixels: 55 µm Periodic position of hole w.r.t. pixel: repeats after 12 pixels
- The frame has a finite thickness
- Difficult to reach a perfect adhesion of the frame to the surface

Timepix cosmics

Timepix cosmics



Snowmass, August, 2005



InGrid

Integrate GEM/Micromegas and pixel sensor by 'wafer post-processing' :

thinness and robustness of the grid

accuracy of the gap (provides excellent resolution and uniformity)

no frame (no loss of active surface)

possibility to fragment the mesh (provides noise reduction and additional localisation usable for zero-suppression)

First step : try the process on bare Si wafers (without CMOS circuit)

'GEM'

'Micromegas'





InGrid process

- 1) Oxide the Si wafer, insulating SiO_2 layer on top
- 2) Deposition of 0.2 μ m of AI for anode, and patterning
- 3) Deposition of 50 μ m photoresist and UV exposure
- 4) Deposition and patterning of the grid: 0.8 μm of pure Al
- 5) Removal of the exposed photoresist

RESULT : a thin mesh (0.8 μ m compared to 3-5 μ m with best standard techniques), sustained at an accurate 50 μ m from the anode.



I NGRI D: some first trials Various pitches, shapes







Snowmass, August, 2005



⁵⁵Fe source 740 MBq Collimated on 1mm diameter

Drift cathode

InGrid wafer

HV connectors to measure mesh, cathode and anode currents, and mesh signal



Result of the process

After 1 year of trials and improvements, a satisfactory InGrid holds the voltage.

Pitch 60 μm

4" wafer with 19 InGrids





After 1 year of trials and improvements: first ⁵⁵Fe signal in an Ingrid detector with He+20%isobutane.



Results with Argon + 20% isobutane



Gain curves

Gains up to O(10⁴) are reached with this first InGrid



Currents

The currents through the cathode, the grid and the anode are measured

This allows a measurement of the ion backflow fraction : O(1%), consistent with the field ratio.





Future

Try various hole size and pitch (19 already available), thinner gaps.

In parallel develop the chip to provide it with time measurement capability (TimePix, Si TPC)

The work on the Si TPC will receive funding from European Community (EUDET project).

~780 k€, plus a commitment of ~1300 k€ from NIKHEF, Saclay and Freiburg in 2006-2009.

Others are welcome to join, even not from Europe.



Conclusion

The first InGrid shows unprecedented performances

Excellent energy resolution

No need for a frame: the mesh is sustained everywhere.

Easy to segment the mesh (thus lowering the capacitance) and to align mesh and pads

Once the process will be fully stabilized, postprocessing onto Medipix2 and Timepix will give a cluster-resolving TPC, very interesting to

- understand further gas ionization and study how Micromegas works

- make a digital TPC